



High Speed SMD Switching Diode

FEATURES

- Fast switching device (trr<4.0ns)
- Surface device type mounting
- Matte Tin(Sn) terminal finish
- Pb free version and RoHS compliant





Hermetically Sealed Glass



ROHS

MECHANICAL DATA

- Case: Mini-MELF Package

- High temperature soldering guaranteed: 270°C/10s

- Polarity: Indicated by black cathode band

- Weight: 31mg (approximately)

MAXIMUM RATINGS AND ELECTRICAL CHA	1	·	1
PARAMETER	SYMBOL	VALUE	UNIT
Power Dissipation	P _D	500	mW
Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Reverse Voltage	V _R	75	V
Peak Forward Surge Current (Note 1)	I _{FSM}	2	А
Non-Repetitive Peak Forward Current	I _{FM}	450	mA
Mean Forward Current	I _{F(AV)}	150	mA
Forward Continuous Current	I _F	150	mA
Repetitive Peak Forward Current	I _{FRM}	450	mA
Thermal Resistance (Junction to Ambient) (Note 2)	$R_{ heta JA}$	300	°C/W
Junction and Storage Temperature Range	Tu. Terc	-65 to +175	ိုင

PARAMETER		SYMBOL	MIN	MAX	UNIT
Poverse Preskdown Veltage	I _R =100μA	$V_{(BR)}$	100	-	V
Reverse Breakdown Voltage	I _R =5μA		75	-	
Forward Voltage		V _F	-	-	V
LL4448, LL914B	I _F =5 mA		0.62	0.72	
LL4148	I _F =50 mA		-	1	
LL4448, LL914B	I _F =100 mA		-	1	
Poverse Leekage Current	V _R =20V	ı	-	25	nA
Reverse Leakage Current	V _R =75V	I _R	-	5	μΑ
Junction Capacitance	V _R =0 f=1.0MHz	CJ	-	4	pF
Reverse Recovery Time	(Note 3)	t _{rr}	-	4	ns

Note 1: Test condition: 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)

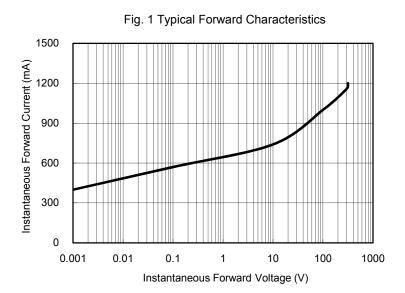
Note 2: Valid provided that electrodes are kept at ambient temperature

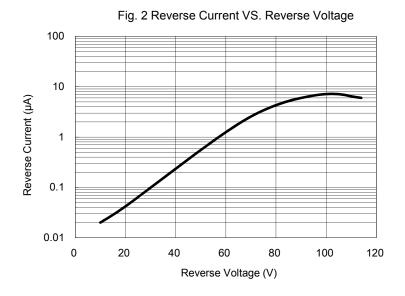
Note 3: Reverse recovery test conditions : $I_F = I_R = 10 \text{mA}$, $R_L = 100 \Omega$, $I_{RR} = 1 \text{mA}$

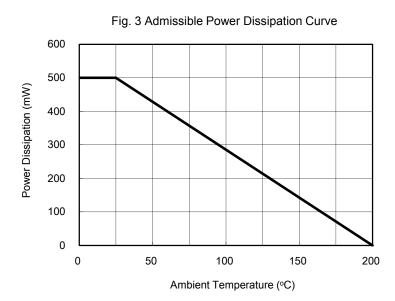


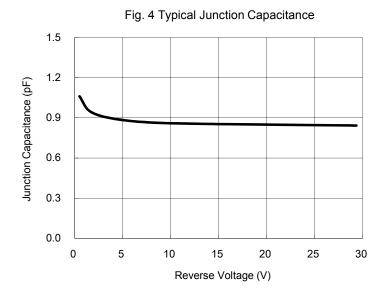
RATINGS AND CHARACTERISTICS CURVES

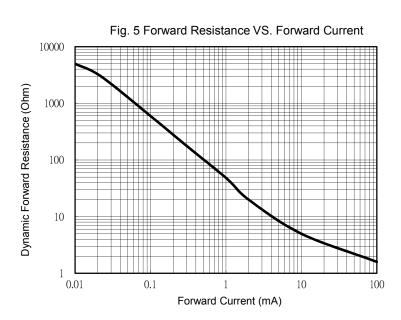
(T_A=25°C unless otherwise noted)









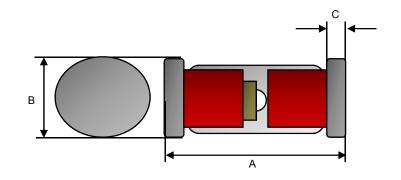




ORDER INFORMATION (EXAMPLE)

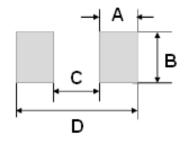


PACKAGE OUTLINE DIMENSION



DIM.	Unit (mm)		Unit (inch)	
DIIVI.	Min	Max	Min	Max
Α	3.30	3.70	0.130	0.146
В	1.40	1.60	0.055	0.063
С	0.20	0.50	0.008	0.020

SUGGEST PAD LAYOUT



DIM.	Unit (mm)	Unit (inch)
DIIVI.	Тур.	Тур.
Α	1.25	0.049
В	2.00	0.079
С	2.50	0.098
D	5.00	0.197





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